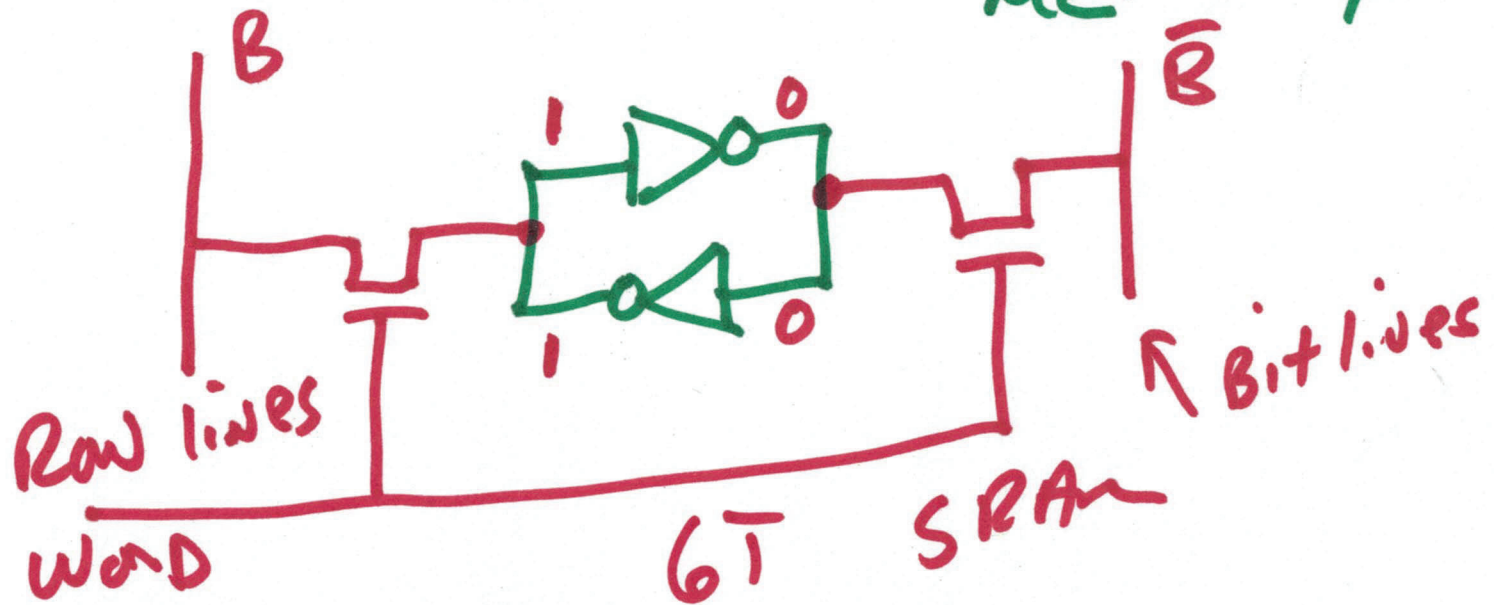


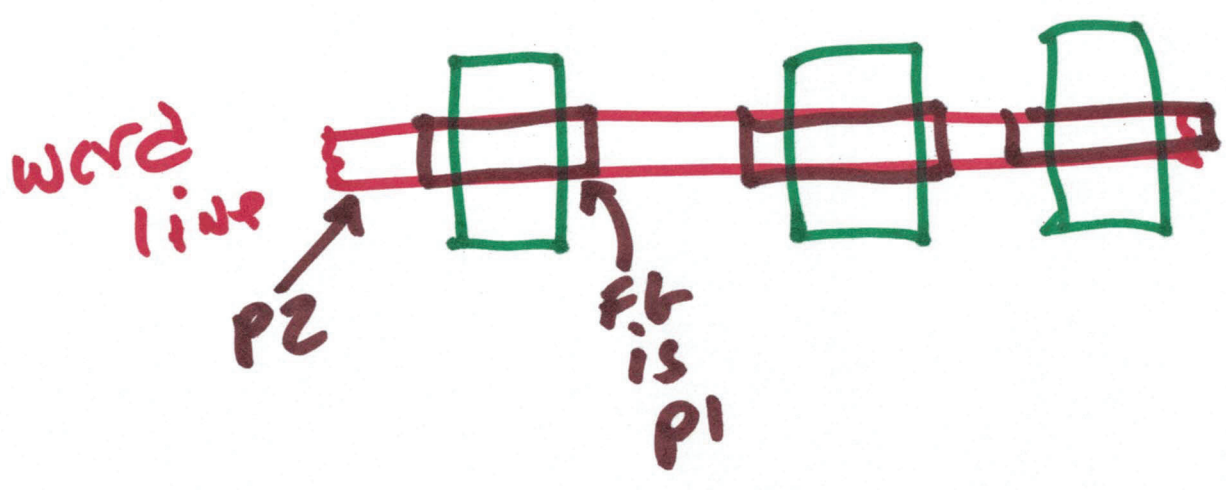
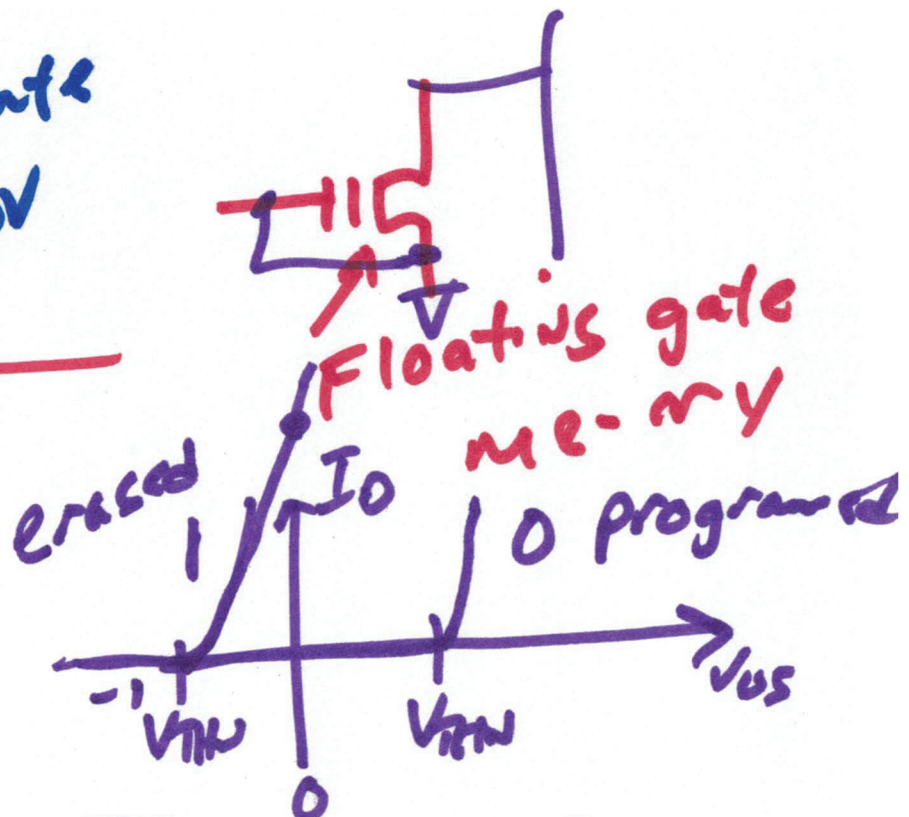
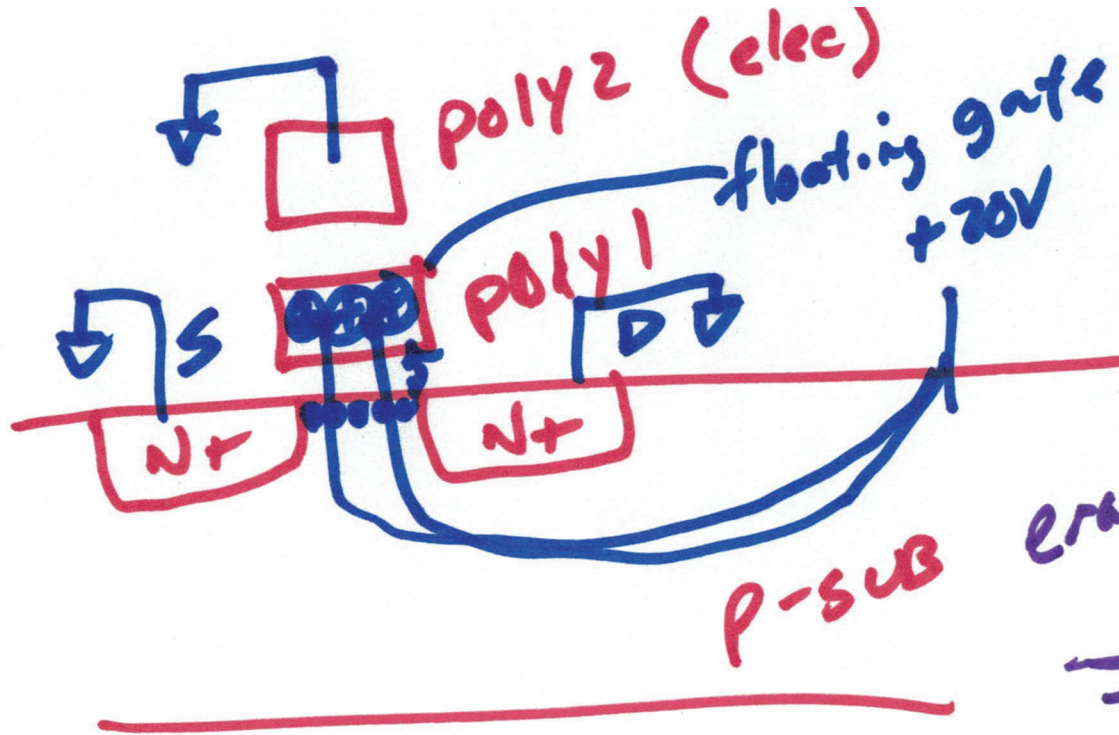
EE 420/ELG621
Digital IC Design

NOV. 29, 2021

Static Random Access
Memory

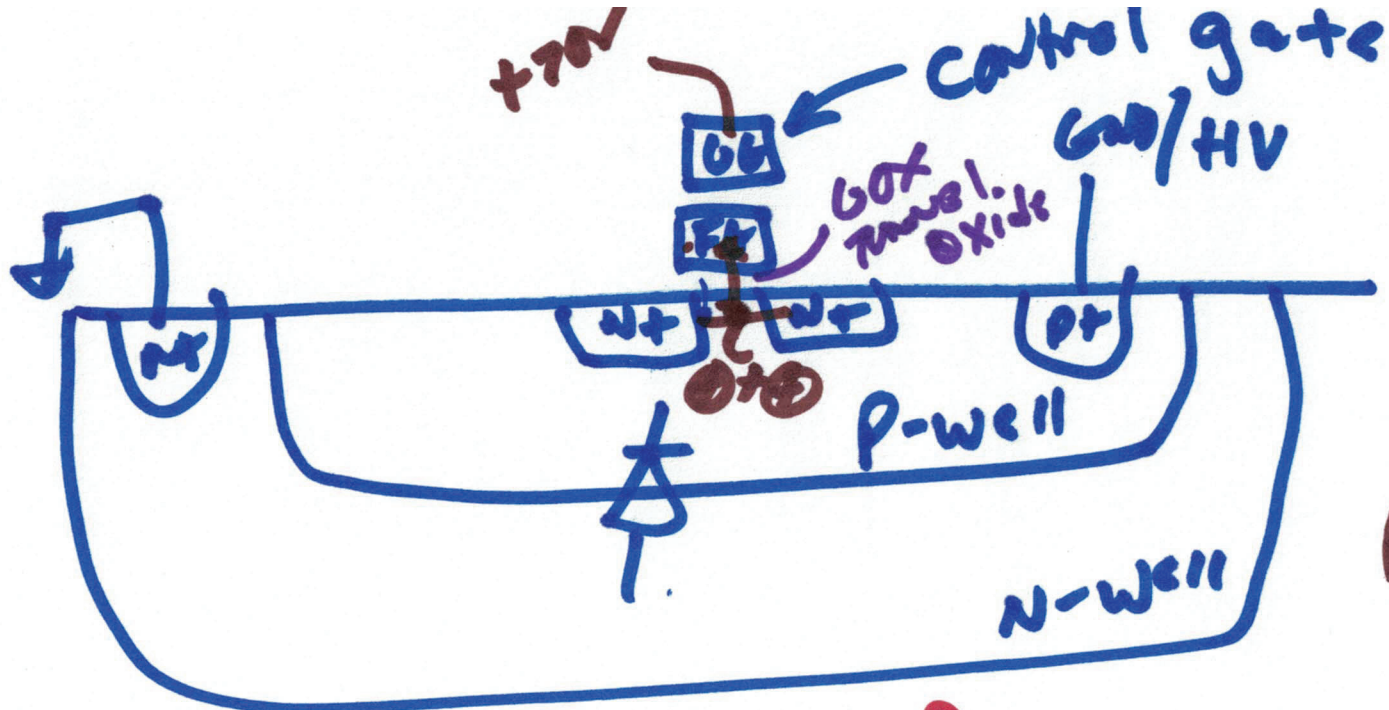


1)



MLC
SLC
1T1C
1T2C
2T2C

2)



ERASED device
 V_{TH} is Negative

PROGRAMMED device

V_{TH} is positive
 p-sub positive

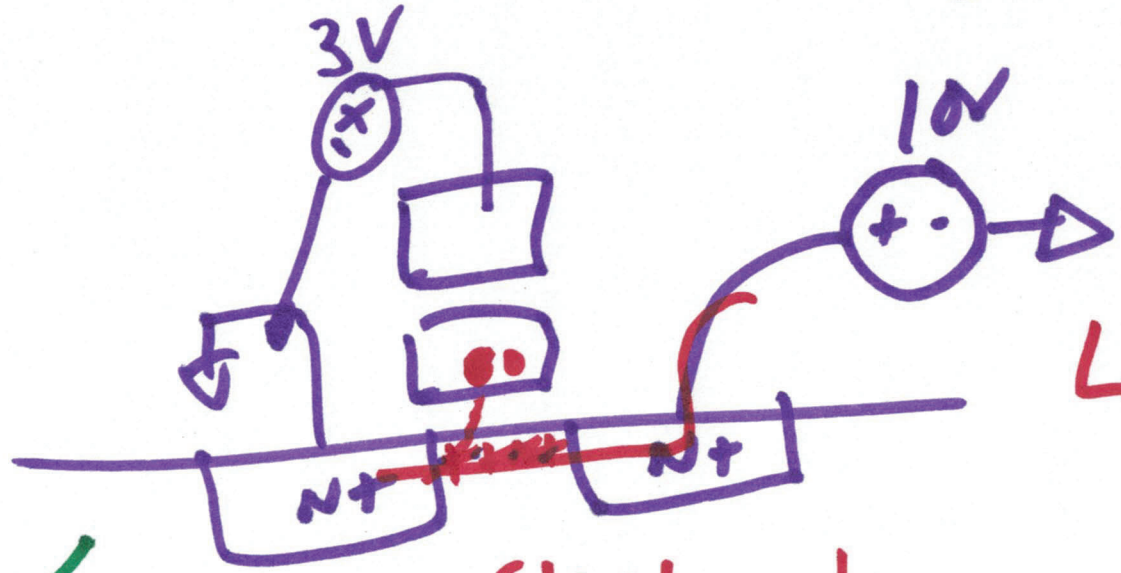


Fowler Nordheim tunneling
 FNT

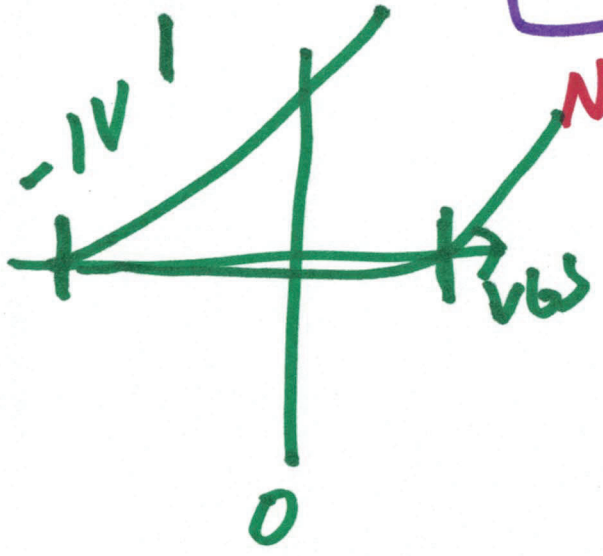
NAND FLASH

3)

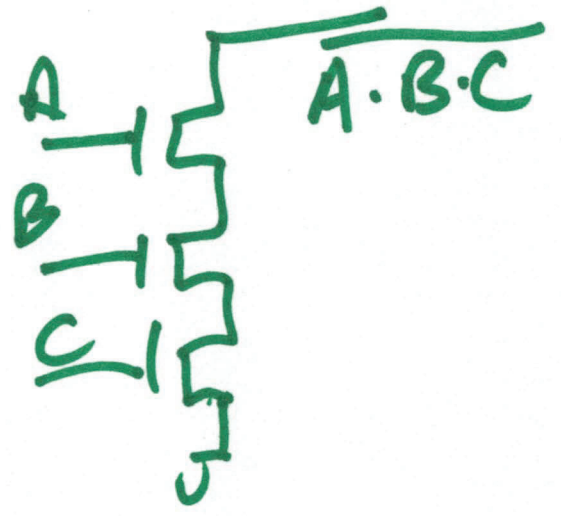
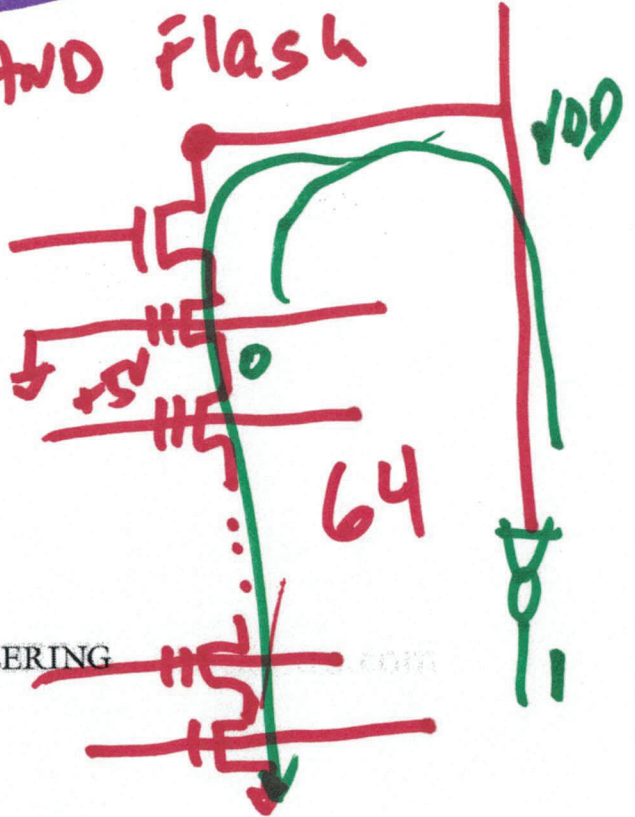
Channel Hot Electron (CHE)



Lucky Electron

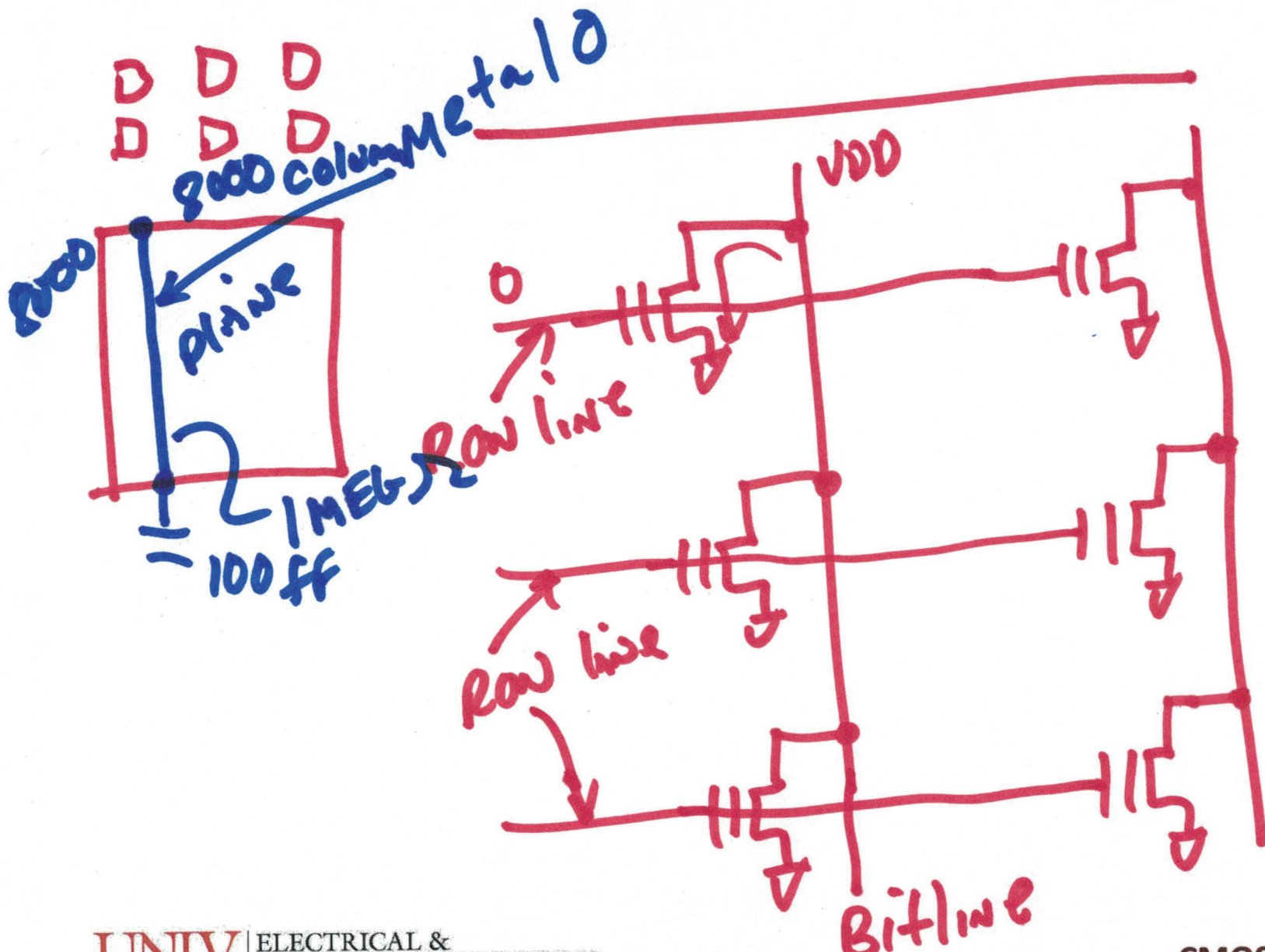


NAND Flash

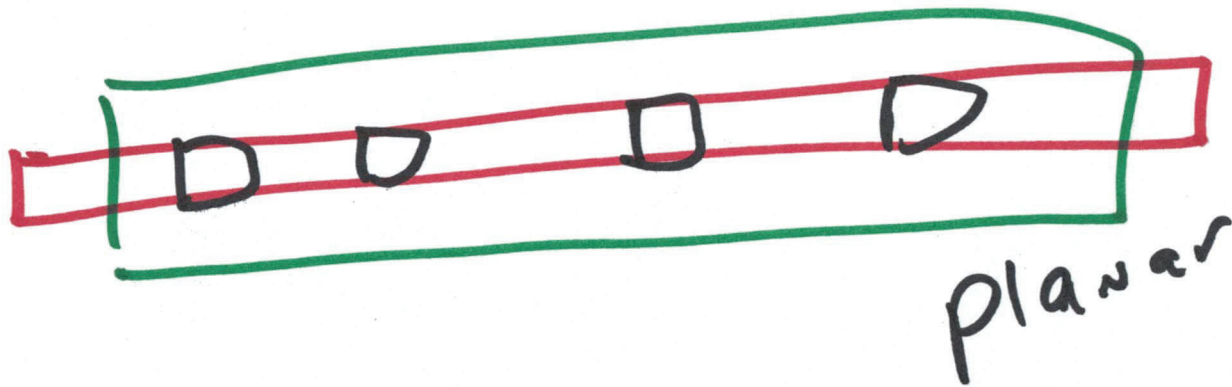
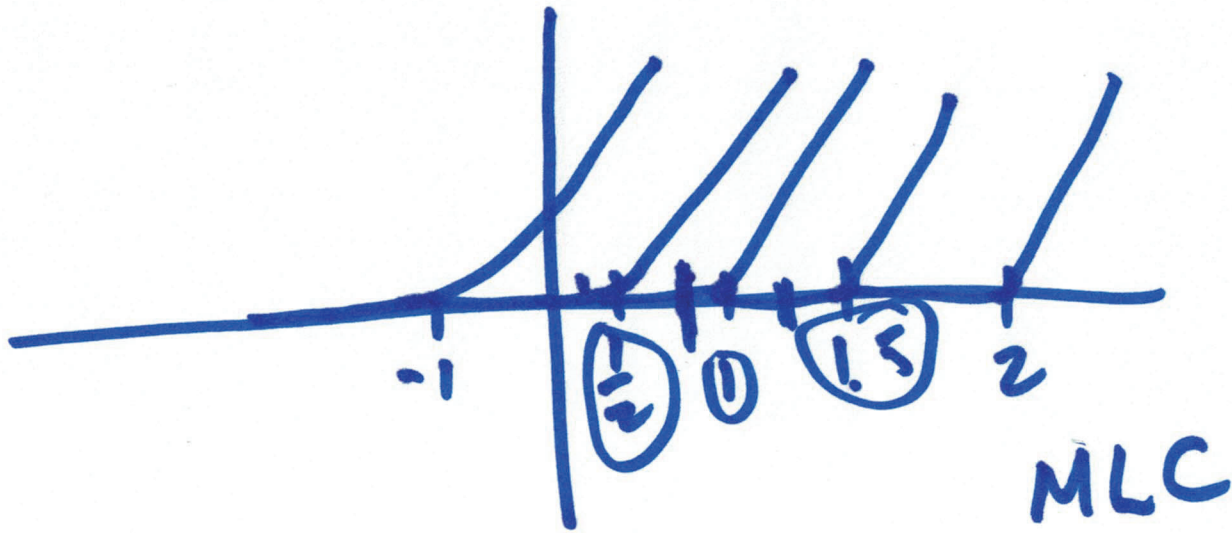


4)

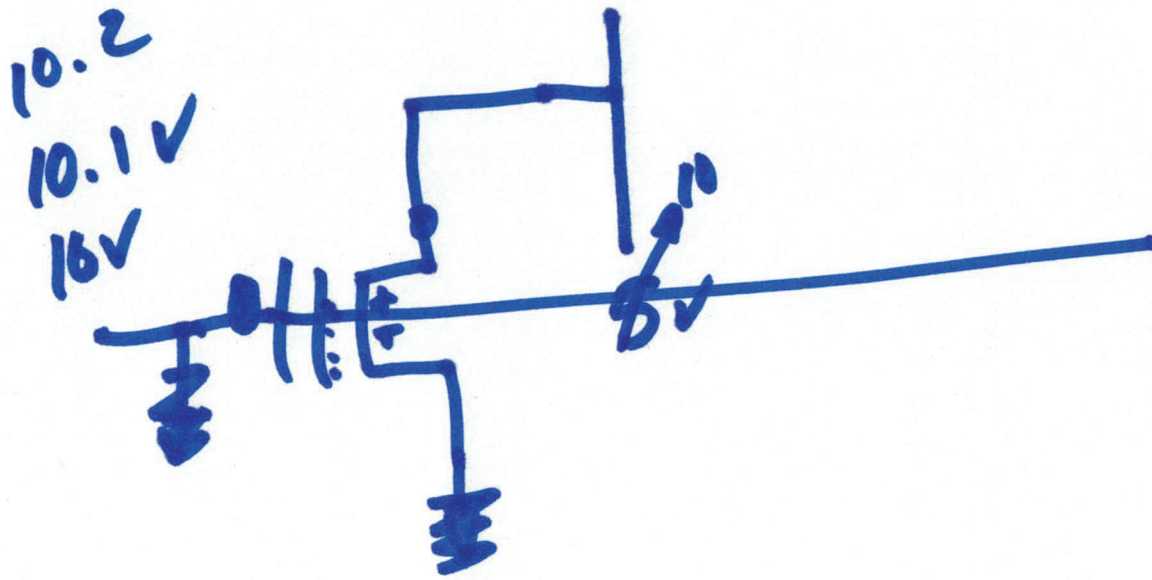
NOR2 Flash Memory



5)



6)



7)